Non-Inverting 3-State Buffer

The NL17SZ125 is a high performance non–inverting buffer operating from a 1.65 V to 5.5 V supply.

Features

- Extremely High Speed: t_{PD} 2.6 ns (typical) at $V_{CC} = 5.0 \text{ V}$
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Overvoltage Tolerant Inputs and Outputs
- LVTTL Compatible Interface Capability With 5.0 V TTL Logic with V_{CC} = 3.0 V
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- 3-State OE Input is Active-Low
- Replacement for NC7SZ125
- Chip Complexity = 36 FETs
- Pb-Free Packages are Available

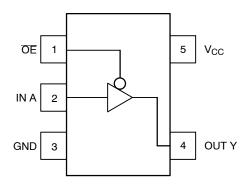


Figure 1. Pinout (Top View)

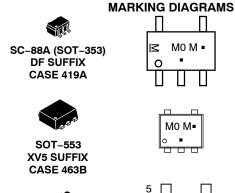


Figure 2. Logic Symbol



ON Semiconductor®

http://onsemi.com







M0 = Specific Device Code
M = Date Code
Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT				
1	ŌE			
2	IN A			
3	GND			
4	OUT Y			
5	V _{CC}			

FUNCTION TABLE

OE Input	A Input	Y Output
L	L	L
L	Н	Н
Н	X	Z

X = Don't Care

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

MAXIMUM RATINGS

Symbol	Param	eter	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage	-0.5 to +7.0	V	
V _{OUT}	DC Output Voltage		-0.5 to +7.0	V
I _{IK}	DC Input Diode Current		-50	mA
lok	DC Output Diode Current		-50	mA
I _{OUT}	DC Output Sink Current		±50	mA
Icc	DC Supply Current per Supply Pin	±100	mA	
T _{STG}	Storage Temperature Range	−65 to +150	°C	
T _L	Lead Temperature, 1 mm from Case for 10	Seconds	260	°C
TJ	Junction Temperature Under Bias		+ 150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 1)	SC-88A/SOT-553 TSOP-5	350 230	°C/W
P_{D}	Power Dissipation in Still Air at 85°C		150	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 N/A	٧

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace with no air flow.

- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	1.65	5.5	V
V _{IN}	DC Input Voltage	0	5.5	V
V _{OUT}	DC Output Voltage	0	5.5	V
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V} \\ V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V} \\ V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V} \\ V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0 0 0	20 20 10 5.0	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

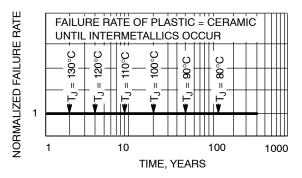


Figure 3. Failure Rate vs. Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

		V _{CC}	T _A = 25°C		С	-55°C ≤ T _A ≤ 125°			
Symbol	Parameter	(V)	Min	Тур	Max	Min	Max	Unit	Condition
V _{IH}	High-Level Input Voltage	1.65 to 1.95 2.3 to 5.5	0.75 V _{CC} 0.7 V _{CC}			0.75 V _{CC} 0.7 V _{CC}		V	
V _{IL}	Low-Level Input Voltage	1.65 to 1.95 2.3 to 5.5			0.25 V _{CC} 0.3 V _{CC}		0.25 V _{CC} 0.3 V _{CC}	V	
V _{OH}	High-Level Output Voltage V _{IN} = V _{IH}	1.65 1.8 2.3 3.0 4.5	1.55 1.7 2.2 2.9 4.4	1.65 1.8 2.3 3.0 4.5		1.55 1.7 2.2 2.9 4.4		V	Ι _{ΟΗ} = -100 μΑ
		1.65 2.3 3.0 3.0 4.5	1.29 1.9 2.4 2.3 3.8	1.52 2.15 2.80 2.68 4.20		1.29 1.9 2.4 2.3 3.8		V	$\begin{split} I_{OH} &= -4 \text{ mA} \\ I_{OH} &= -8 \text{ mA} \\ I_{OH} &= -16 \text{ mA} \\ I_{OH} &= -24 \text{ mA} \\ I_{OH} &= -32 \text{ mA} \end{split}$
V _{OL}	Low-Level Output Voltage V _{IN} = V _{IL}	1.65 1.8 2.3 3.0 4.5		0.0 0.0 0.0 0.0 0.0	0.1 0.1 0.1 0.1 0.1		0.1 0.1 0.1 0.1 0.1	V	Ι _{ΟL} = 100 μΑ
		1.65 2.3 3.0 3.0 4.5		0.08 0.10 0.15 0.22 0.22	0.24 0.30 0.40 0.55 0.55		0.24 0.30 0.40 0.55 0.55	V	$\begin{aligned} &I_{OL} = 4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \\ &I_{OL} = 16 \text{ mA} \\ &I_{OL} = 24 \text{ mA} \\ &I_{OL} = 32 \text{ mA} \end{aligned}$
I _{IN}	Input Leakage Current	0 to 5.5			±1.0		±1.0	μΑ	$0 \text{ V} \leq V_{\text{IN}} \leq 5.5 \text{ V}$
l _{OZ}	3-State Output Leakage	1.65 to 5.5			±0.5		±5.0	μΑ	$\begin{array}{c} V_{IN} = V_{IH} \text{ or } V_{IL} \\ 0 \text{ V} \leq V_{OUT} \leq 5.5 \text{ V} \end{array}$
I _{OFF}	Power Off Leakage Current	0.0			1.0		10	μΑ	V _{IN} or V _{OUT} = 5.5 V
I _{CC}	Quiescent Supply Current	1.65 to 5.5			1.0		10	μΑ	V _{IN} = 5.5 V, GND

AC ELECTRICAL CHARACTERISTICS ($t_R = t_F = 3.0 \text{ ns}$)

				V _{cc}	T,	_λ = 25°	С	-55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Condition	on	(V)	Min	Тур	Max	Min	Max	Unit
t _{PLH}	Propagation Delay	$R_L = 1 M\Omega$	C _L = 15 pF	1.8 ± 0.15	2.0	9.0	10	2.0	10.5	ns
t _{PHL}	AN to YN (Figures 4 and 5, Table 1)	$R_L = 1 M\Omega$	C _L = 15 pF	2.5 ± 0.2	1.0		7.5	1.0	8.0	
		$\begin{aligned} R_L &= 1 \ M\Omega \\ R_L &= 500 \ \Omega \end{aligned}$	C _L = 15 pF C _L = 50 pF	3.3 ± 0.3	0.8 1.2		5.2 5.7	0.8 1.2	5.5 6.0	
		R_L = 1 MΩ R_L = 500 Ω	C _L = 15 pF C _L = 50 pF	5.0 ± 0.5	0.5 0.8		4.5 5.0	0.5 0.8	4.8 5.3	
t _{PZH}	Output Enable Time	R _L = 250 Ω	C _L = 50 pF	1.8 ± 0.15	2.0	7.6	9.5	2.0	10	ns
t _{PZL}	(Figures 6, 7and 8, Table 1)			2.5 ± 0.2	1.8		8.5	1.8	9.0	
				3.3 ± 0.3	1.2		6.2	1.2	6.5	
				5.0 ± 0.5	0.8		5.5	0.8	5.8	
t _{PHZ}	Output Disable Time	R_L and R_1 = 500 Ω	2 C _L = 50 pF	1.8 ± 0.15	2.0	8.0	10	2.0	10.5	ns
t _{PLZ}	(Figures 6, 7and 8, Table 1)	Figures 6, 7and 8, Table 1)	2.5 ± 0.2	1.5		8.0	1.5	8.5		
				3.3 ± 0.3	0.8		5.7	0.8	6.0	
				5.0 ± 0.5	0.3		4.7	0.3	5.0	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_{I} = 0 \text{ V or } V_{CC}$	2.5	pF
C _{OUT}	Output Capacitance	$V_{CC} = 5.5 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	2.5	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, $V_{CC} = 3.3 \text{ V}$, $V_I = 0 \text{ V or } V_{CC}$ 10 MHz, $V_{CC} = 5.5 \text{ V}$, $V_I = 0 \text{ V or } V_{CC}$	9 11	pF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

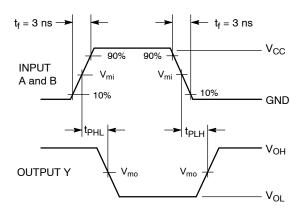
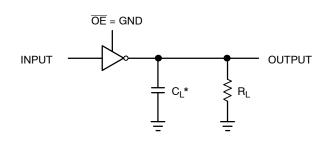


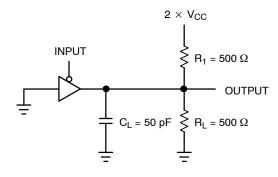
Figure 4. Switching Waveform



*Includes all probe and jig capacitance.

A 1 MHz square input wave is recommended for propagation delay tests.

Figure 5. T_{PLH} or T_{PHL}



A 1 MHz square input wave is recommended for propagation delay tests.

V_{CC} OUTPUT $\frac{1}{1 - 1} C_{L} = 50 \text{ pF}$ $R_{L} = 250 \Omega$

A 1 MHz square input wave is recommended for propagation delay tests.

Figure 6. T_{PZL} or T_{PL}

Figure 7. T_{PZH} or T_{PHZ}

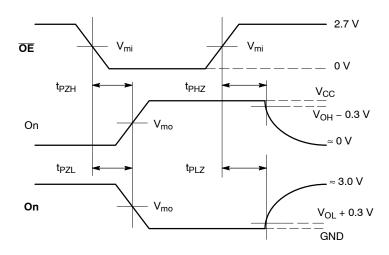


Figure 8. AC Output Enable and Disable Waveform

Table 1. OUTPUT ENABLE AND DISABLE TIMES

 t_R = t_F = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns

	V _{CC}					
Symbol	3.3 V ± 0.3 V	2.7 V	2.5 V ± 0.2 V			
V _{mi}	1.5 V	1.5 V	V _{CC/} 2			
V _{mo}	1.5 V	1.5 V	V _{CC/} 2			

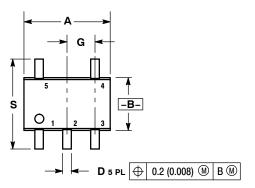
DEVICE ORDERING INFORMATION

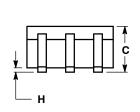
Device	Package	Shipping [†]
NL17SZ125DFT2	SC-88A (SOT-353)	3000 / Tape & Reel
NL17SZ125DFT2G	SC-88A (SOT-353) (Pb-Free)	3000 / Tape & Reel
NL17SZ125XV5T2G	SOT-553 (Pb-Free)	4000 / Tape & Reel
NL17SZ125DTT1G	SOT23-5 (Pb-Free)	3000 / Tape & Reel

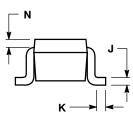
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC-88A, SOT-353, SC-70 CASE 419A-02 **ISSUE J**







- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

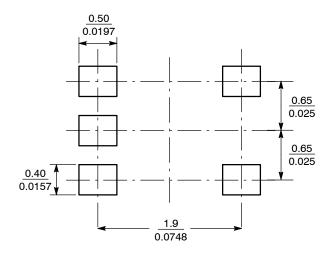
 2. CONTROLLING DIMENSION: INCH.

 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.

 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIN	IETERS	
DIM	MIN MAX		MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65 BSC		
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	0.008 REF		0.20 REF		
S	0.079	0.087	2.00	2.20	

SOLDERING FOOTPRINT*

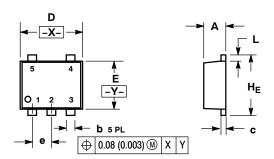


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-553, 5 LEAD CASE 463B-01

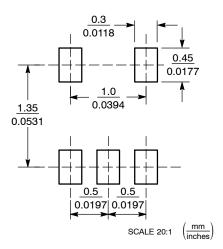
ISSUE B



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES
 LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	MOM	MAX
Α	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.13	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.063	0.067
E	1.10	1.20	1.30	0.043	0.047	0.051
е	0.50 BSC				0.020 BSC)
L	0.10	0.20	0.30	0.004	800.0	0.012
HE	1.50	1.60	1.70	0.059	0.063	0.067

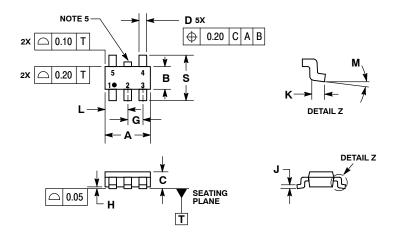
SOLDERING FOOTPRINT*



^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSOP-5 CASE 483-02 **ISSUE H**



- NOTES:

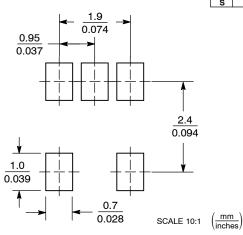
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. MAXIMUM LEAD THICKNESS INCLUDES
- LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
- OF BASE MATERIAL.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS
- OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS	
DIM	MIN	MAX
Α	3.00 BSC	
В	1.50 BSC	
С	0.90	1.10
D	0.25	0.50
G	0.95 BSC	
Н	0.01	0.10
J	0.10	0.26
Κ	0.20	0.60
L	1.25	1.55
М	0 °	10°
S	2.50	3.00

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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